

Serial No. 09/856,212

IN THE CLAIMS:

Please amend the claims 9, 10 and 11 as follows:

1-8. (canceled)

9. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, comprising ~~the steps~~ a first step of maintaining a first heat treatment temperature ~~at the~~ for an initial entry of the silicon single crystal wafer ~~to be a target of the heat treatment is at less than~~ up to 500°C, and a second step of maintaining a temperature ramping rate in a temperature range from the first heat treatment temperature ~~at initial entry to a maximum~~ second heat treatment temperature ~~in a range~~ of 700°C-900°C, said ramping rate being 1°C/min or less.

10. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, comprising ~~the steps~~ a first step of maintaining a first heat treatment temperature ~~at the~~ for an initial entry of the silicon single crystal wafer ~~to be a target of the heat treatment is at less than~~ up to 500°C, and a second step of maintaining a temperature ramping rate in a temperature range from the first heat treatment temperature ~~at initial entry to a maximum~~ second heat treatment temperature ~~in a range~~ of 700°C-900°C, said ramping rate being 1C/min or less, so as to make uniform the distribution of an oxide precipitate density of the silicon single crystal wafer ~~after heat treatment~~.

11. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, comprising ~~the steps~~ a first step of controlling a first heat treatment temperature ~~at the~~ for an initial entry of the silicon single crystal wafer to be a target of the heat treatment and a second step of controlling a temperature ramping rate from the

heat treatment temperature at initial entry to a ~~maximum~~ higher second heat treatment temperature and maintaining in a range of 700°C-900°C so as to ~~adjust~~ make the distribution of an oxide precipitate density of the silicon single crystal wafer more uniform after heat treatment.

12. (original) The method according to Claim 9, wherein the oxygen concentration of the perfect crystal is 13×10^{17} atoms/cm³ or less.

13. (previously presented) A silicon single crystal wafer produced by the method according to Claim 12.

14-23 (canceled)